

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Atty. Docket

KARS-MICHIEL H. LENSSEN ET AL

NL 000361

Serial No.

Filed: CONCURRENTLY

MAGNETIC MULTILAYER STRUCTURE WITH IMPROVED MAGNETIC FIELD RANGE

Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please  
amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

4. (Amended) Device as claimed in claim 1, in which each of the intermediate layers of the AAF is a Ru layer.
5. (Amended) Device as claimed in claim 1, in which the exchange biasing layer is arranged between the substrate and the AAF layer system.
6. (Amended) Device as claimed in claim 1, wherein within the odd number of non-adjacent ferromagnetic layers form a stack of layers.

9. (Amended) Data storage system including a magneto-resistive device according to claim 1.


10. (Amended) Magnetic memory including a magneto-resistive device according to claim 1.

REMARKS

The claims have been amended in order to reformat the claims to delete all multiple dependencies prior to calculation of the filing fee and place the instant application in standard U.S. format.

Entry of this amendment prior to calculating the filing fee is respectfully requested.

Respectfully submitted,

  
By \_\_\_\_\_  
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June 19, 2001

## APPENDIX

4. (Amended) Device as claimed in claim 1 ~~or 2~~, in which each of the intermediate layers of the AAF is a Ru layer.
5. (Amended) Device as claimed in claim 1 ~~any of the claims 1 to 4~~, in which the exchange biasing layer is arranged between the substrate and the AAF layer system.
6. (Amended) Device as claimed in claim 1 ~~any of the claims 1 to 5~~, wherein within the odd number of non-adjacent ferromagnetic layers form a stack of layers.
9. (Amended) Data storage system including a magneto-resistive device according to claim 1 ~~any one of the preceding claims 1 to 8~~.
10. (Amended) Magnetic memory including a magneto-resistive device according to claim 1 ~~any one of the preceding claims 1 to 8~~.